O. P. Dolgolenko

CONFIGURATION TRANSITIONS OF DIVACANCIES IN SILICON AND GERMANIUM

High-resistance samples p-Si ($p_0 = (1.63 - 7.09)\cdot 10^{11}$ cm^{-3}) and n-Si ($n_0 = 1.19\cdot 10^{14}$ cm^{-3}), grown by the floating zone melting after irradiation with fast neutron reactor at 320 °C after isothermal and isochronal annealing were studied. The energy levels of divacancy in three charge states, depending on its configuration are determined. Values of the energy levels of divacancies and A - center after their modification background impurities are considered.

Keywords: silicon, germanium, fast neutron, divacancy.